



Cypress Semiconductor Corporation, 198 Champion Court, San Jose, CA 95134. Tel: (408) 943-2600

PRODUCT INFORMATION NOTIFICATION

PIN: PIN163705

Date: October 04, 2016

Subject: Updates to Timing Parameters for ASO Mode Entry on 65nm GL-S NOR Flash Memory Devices

To:

Change Type: Minor

Product Information:

Cypress is updating the 65nm GL-S family datasheet with the required timing for the command cycle to enter the ASO modes. (ASO=Address Space Overlay, mapping of non-array data into the address space, for e.g. CFI, DYB, or PPB.) This update clarifies the timing parameters thereby avoiding any incorrect data read from the device after exiting an ASO in the device.

This change does not affect the form, fit and function of the device. Functionality specifications remain unchanged. Refer to the attached datasheet page 84 for the updates. Below table summarizes the datasheet update.

Page / Section	Parameters	From	To
84, 10.4.2	ASO Entry Timing	-	Addition of Table 10.9 and Figure 10.17

Part Numbers Affected:

This update is applicable to all MPNs as per this datasheet (Refer Section 13)

Approximate Implementation Date:

Revised datasheets are now live on www.cypress.com . Please visit the corresponding product page to download the latest copy.

Anticipated Impact:

None. There is no change to the product. Products manufactured with updated datasheet parameters are completely compatible with existing product from a functional, parametric, and quality performance perspective. The updated datasheet is a clarification on proper timing requirements for ASO Entry Mode.

Cypress also recommends that customers take this opportunity to review these changes against current application notes, system design considerations and customer environment conditions to assess impact (if any) to their application.

Method of Identification:

Cypress maintains traceability of product to wafer level, including wafer fabrication location, through the lot number marked on the package.

Response Required:

This is an information only announcement. No response is required

For additional information regarding this change, contact your local sales representative or contact the PCN Administrator at pcn_adm@cypress.com.

Sincerely,

Cypress PCN Administration

288	S29GL512S11TFI023	512 MBIT, 3V, 110NS, 56-LEAD TSOP, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, LOWEST ADDRESS SECTOR PROTECTED	512 Mb	GL
289	S29GL512S11TFIV10	512 MBIT, 3V, 110NS, 56-LEAD TSOP, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, VIO, HIGHEST ADDRESS SECTOR PROTECTED	512 Mb	GL
290	S29GL512S11TFIV13	512 MBIT, 3V, 110NS, 56-LEAD TSOP, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, VIO, HIGHEST ADDRESS SECTOR PROTECTED	512 Mb	GL
291	S29GL512S11TFIV20	512 MBIT, 3V, 110NS, 56-LEAD TSOP, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, VIO, LOWEST ADDRESS SECTOR PROTECTED	512 Mb	GL
292	S29GL512S11TFIV23	512 MBIT, 3V, 110NS, 56-LEAD TSOP, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, VIO, LOWEST ADDRESS SECTOR PROTECTED	512 Mb	GL
293	S29GL512S11TFV010	512 MBIT, 3V, 110NS, 56-LEAD TSOP, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, HIGHEST ADDRESS SECTOR PROTECTED	512 Mb	GL
294	S29GL512S11TFV013	512 MBIT, 3V, 110NS, 56-LEAD TSOP, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, HIGHEST ADDRESS SECTOR PROTECTED	512 Mb	GL
295	S29GL512S11TFV020	512 MBIT, 3V, 110NS, 56-LEAD TSOP, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, LOWEST ADDRESS SECTOR PROTECTED	512 Mb	GL
296	S29GL512S11TFV023	512 MBIT, 3V, 110NS, 56-LEAD TSOP, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, LOWEST ADDRESS SECTOR PROTECTED	512 Mb	GL
297	S29GL512S11WEIV19	512 MBIT, 3V, 110NS, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, VIO, HIGHEST ADDRESS SECTOR PROTECTED	512 Mb	GL
298	S29GL512S12DHBV10	512 MBIT, 3V, 120NS, 64-BALL FBGA, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, VIO, HIGHEST ADDRESS SECTOR PROTECTED	512 Mb	GL
299	S29GL512S12DHIV10	512 MBIT, 3V, 120NS, 64-BALL FBGA, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, VIO, HIGHEST ADDRESS SECTOR PROTECTED	512 Mb	GL
300	S29GL512S12DHIV20	512 MBIT, 3V, 120NS, 64-BALL FBGA, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, VIO, LOWEST ADDRESS SECTOR PROTECTED	512 Mb	GL
301	S29GL512S12FHIV20	512 MBIT, 3V, 120NS, 64-BALL FBGA, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, VIO, LOWEST ADDRESS SECTOR PROTECTED	512 Mb	GL
302	S29GL512S12TFBV10	512 MBIT, 3V, 120NS, 56-LEAD TSOP, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, HIGHEST ADDRESS SECTOR PROTECTED	512 Mb	GL
303	S29GL512S12TFBV20	512 MBIT, 3V, 120NS, 56-LEAD TSOP, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, LOWEST ADDRESS SECTOR PROTECTED	512 Mb	GL
304	S29GL512S12TFIV10	512 MBIT, 3V, 120NS, 56-LEAD TSOP, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, VIO, HIGHEST ADDRESS SECTOR PROTECTED	512 Mb	GL
305	S29GL512S12TFIV20	512 MBIT, 3V, 120NS, 56-LEAD TSOP, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, VIO, LOWEST ADDRESS SECTOR PROTECTED	512 Mb	GL
306	S29GL512S12TFV20	512 MBIT, 3V, 120NS, 56-LEAD TSOP, PAGE MODE FLASH MEMORY FEATURING 65 NM MIRRORBIT PROCESS TECHNOLOGY, LOWEST ADDRESS SECTOR PROTECTED WITH VIO	512 Mb	GL